

INFRARED DIODE LASER AT 808nm

RN-III-808L/1~100mW

产品描述

It features ultra compact design, long lifetime, cost-effectiveness and easy operation. They are used in measurement, communication, spectrum analysis, etc.

产品参数

RN-III-808L/1~100mW		
Central wavelength (nm)	808±3	
Operating mode	CW	
Output power (mW)	>1, 10, 20, ..., 100	
Power stability (rms, over 4 hours)	<1%, <2%, <3% (<0.5%, optional)	
Transverse mode	Near TEM ₀₀	
Dimensions of beam at the aperture (1/e ² ,mm)	~3.5	
Beam divergence, full angle (mrad)	<1.0	
Polarization ratio	>50:1 (>100:1, optional) Horizontal±5 degree (Vertical Optional)	
Warm-up time (minutes)	<5	
Pointing stability after warm-up (mrad)	<0.05	
Beam height from base plate (mm)	24.8	
Operating temperature (°C)	10~35	
Power supply	85-264VAC	PSU-III-LED/ PSU-III-FDA (Frequency for 1Hz-30kHz)
	100-240VAC	PSU-A-D (Frequency for 30kHz -100kHz)
TTL / Analog modulation	TTL or Analog with 1Hz-1kHz 1kHz-10kHz, 10kHz-30kHz, 30kHz-100kHz optional	
Expected lifetime (hours)	10000	
Warranty	1 year	